

# 2SJ0672

## Silicon P-channel MOSFET

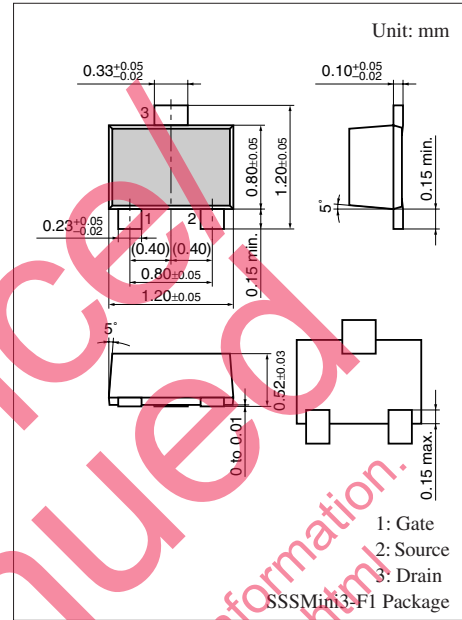
For switching circuits

### ■ Features

- Ultra small package switching MOSFETs
- SSS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source voltage	$V_{DS}$	-30	V
Gate-source voltage (Drain open)	$V_{GSO}$	$\pm 7$	V
Drain current	$I_D$	-100	mA
Peak drain current	$I_{DP}$	-200	mA
Drain power dissipation	$P_D$	100	mW
Channel temperature	$T_{ch}$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$



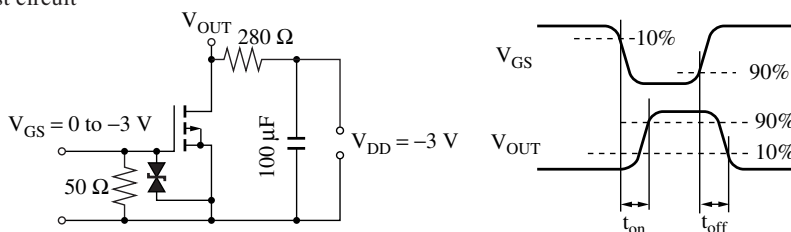
Marking Symbol: 5M

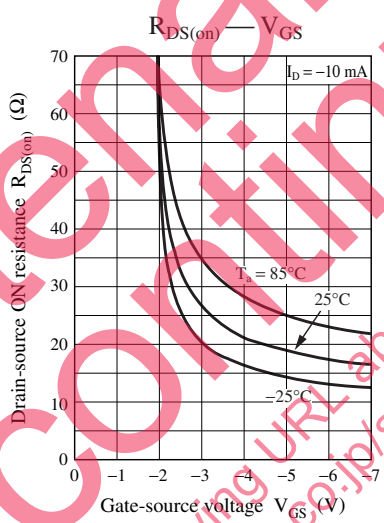
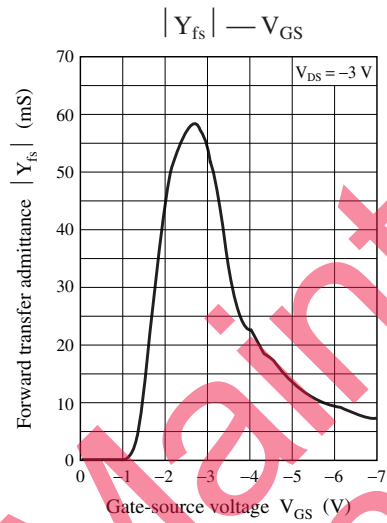
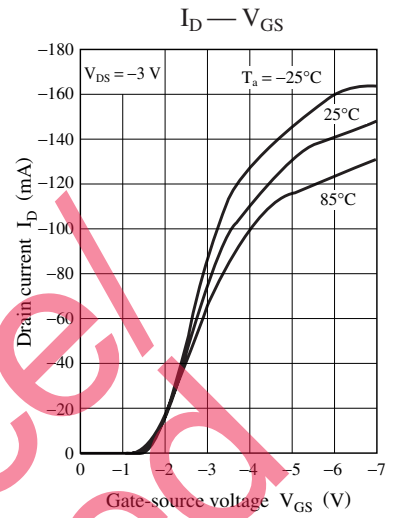
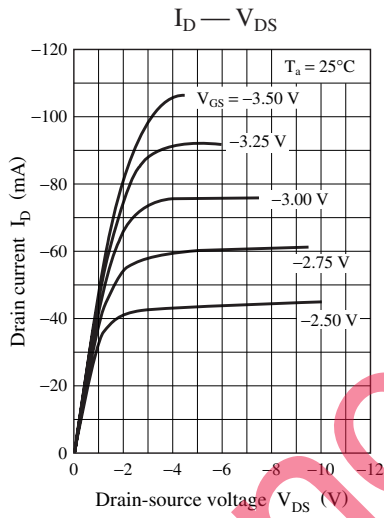
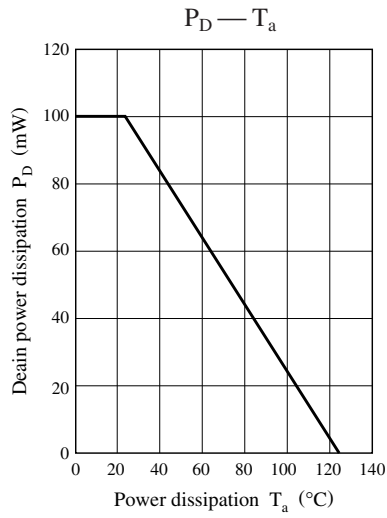
### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	$V_{DSS}$	$I_D = -10 \mu\text{A}, V_{GS} = 0$	-30			V
Drain-source cutoff current	$I_{DSS}$	$V_{DS} = -20 \text{ V}, V_{GS} = 0$			-0.1	$\mu\text{A}$
Gate-source cutoff current	$I_{GSS}$	$V_{GS} = \pm 7 \text{ V}, V_{DS} = 0$			$\pm 10$	$\mu\text{A}$
Gate threshold voltage	$V_{th}$	$V_{DS} = -3.0 \text{ V}, I_D = -1.0 \mu\text{A}$	-0.5	-1.0	-1.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3 \text{ V}, I_D = 10 \text{ mA}, f = 1 \text{ kHz}$	20	35		mS
Drain-source ON resistance	$R_{DS(on)}$	$V_{GS} = -2.5 \text{ V}, I_D = -10 \text{ mA}$		20	45	$\Omega$
		$V_{GS} = -4.0 \text{ V}, I_D = -10 \text{ mA}$		15	30	
Short-circuit forward transfer capacitance (Common source)	$C_{iss}$	$V_{DS} = -3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		10		pF
Short-circuit output capacitance (Common source)	$C_{oss}$			7		
Reverse transfer capacitance (Common source)	$C_{rss}$			3		
Turn-on time *	$t_{on}$	$V_{DD} = -3 \text{ V}, V_{GS} = 0 \text{ V} \sim -3 \text{ V}$ $I_D = -10 \text{ mA}$		850		ns
Turn-off time *	$t_{off}$	$V_{DD} = -3 \text{ V}, V_{GS} = -3 \text{ V} \sim 0 \text{ V}$ $I_D = -10 \text{ mA}$		850		ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*:  $t_{on}, t_{off}$  test circuit





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